

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n
1	BRS	L22	8	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3) same (EDTA)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:02		0
2	BRS	L23	2	"20020102852"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:08		0
3	BRS	L24	69	("N,N-Bis(2-hydroxyphenyl)ethylenediimino diacetic acid" or (HPED) or "triethylenetetranitrilohexaacetic" or (TTHA) or "desferriferrioxamin B" or "N,N,N Tris[2-(N-hydroxycarbomyl)ethyl]-1,3,5-benzene tricarboxamide" (BAMTH)or "molybdic") same (clean\$3 or etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:13		0
4	BRS	L25	4306	("N,N-Bis(2-hydroxyphenyl)ethylenediimino diacetic acid" or (HPED) or "triethylenetetranitrilohexaacetic" or (TTHA) or "desferriferrioxamin B" or "N,N,N Tris[2-(N-hydroxycarbomyl)ethyl]-1,3,5-benzene tricarboxamide" (BAMTH)or "molybdic" or "ethylenediaminetetraacetic" or (EDTA)) same (clean\$3 or etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:13		0
5	BRS	L26	1319	("N,N-Bis(2-hydroxyphenyl)ethylenediimino diacetic acid" or (HPED) or "triethylenetetranitrilohexaacetic" or (TTHA) or "desferriferrioxamin B" or "N,N,N Tris[2-(N-hydroxycarbomyl)ethyl]-1,3,5-benzene tricarboxamide" (BAMTH)or "molybdic" or "ethylenediaminetetraacetic" or (EDTA)) with (clean\$3 or etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:47		0
6	BRS	L27	886	26 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:10		0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Count
7	BRS	L49	21	27 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:11		0
8	IS&R	L50	2	("4,554,050").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:47		0
9	BRS	L51	114	27 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:51		0
10	BRS	L52	221	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3) same (dissolv\$4) same (helium or He or argon or Ar or nitrogen or "N.sub.2" or oxygen or "O.sub.2" or ozone or "O.sub.3" or hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:17		0
11	BRS	L53	126	52 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:18		0
12	BRS	L55	4	53 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:19		0
13	BRS	L54	19	53 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:19		0
14	BRS	L56	1831	((etch\$3 or clean\$3) with (dissolv\$4) with (helium or He or argon or Ar or nitrogen or "N.sub.2" or oxygen or "O.sub.2" or ozone or "O.sub.3" or hydrogen or "H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:17		0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t	E r r o r D e f i n i t i o n	E r r o r s
15	BRS	L57	1153	56 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:18			0
16	BRS	L59	117	57 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:28			0
17	BRS	L58	87	57 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:19			0
18	BRS	L60	1066	57 not 58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:28			0
19	BRS	L61	108	59 not 58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:01			0
20	BRS	L62	1	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3) same (degas\$3 with (water or "H.sub.2O"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:13			0
21	BRS	L63	38	(wafer or semiconductor or substrate))same (etch\$3 or clean\$3) same (degas\$3 with (water or "H.sub.2O")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:13			0